INCORPORATED

Product Summary

V _{(BR)DSS}	R _{DS(ON)}	I _D T _A = +25°C		
40V	0.05Ω @ $V_{GS} = 10V$	7A		

Description

This new generation MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- DC-DC Converters
- Audio Output Stages
- · Relay and Solenoid Driving
- Motor Control

Features

- Low On-Resistance
- · Fast Switching Speed
- Low Threshold
- Low Gate Drive
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

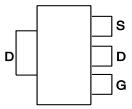
Mechanical Data

- Case: SOT223
- Case Material: Molded Plastic, UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe;
 Solderable per MIL-STD-202, Method 208 63
- Weight: 0.112 grams (Approximate)

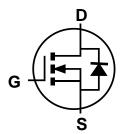




Top View



Pin Out - Top View



Equivalent Circuit

Ordering Information (Note 4)

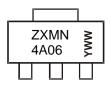
Part Number	Compliance	Case	Packaging
ZXMN4A06GTA	Standard	SOT223	1,000/Tape & Reel

Note:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information

SOT223



ZXMN 4A06 = Product Type Marking Code YWW = Date Code Marking Y or \overline{Y} = Last Digit of Year (ex: 5= 2015) WW or $\overline{W}W$ = Week Code (01~53)



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	40	V
Gate-Source Voltage			V_{GS}	±20	V
		(Note 6)		7	
Continuous Drain Current	$V_{GS} = 10V$	$T_A = +70^{\circ}C \text{ (Note 6)}$	I_{D}	5.6	Α
		(Note 5)		5	
Pulsed Drain Current	V _{GS} = 10V	(Note 7)	I _{DM}	22	Α
Continuous Source Current (Body Diode) (Note 6)		(Note 6)	I _S	5.4	А
Pulsed Source Current (Body Diode) (Note 7)		I _{SM}	22	А	

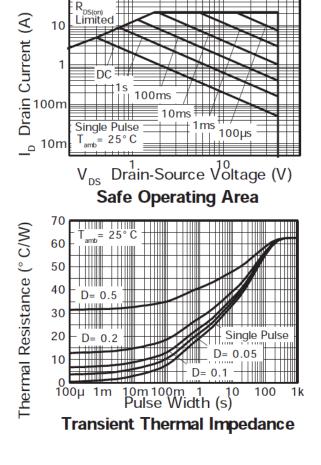
Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

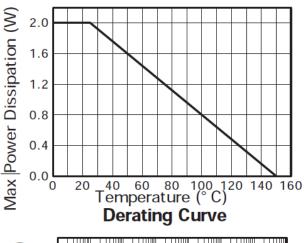
Characteristic		Symbol	Value	Unit	
Power Dissipation	(Note 5)		2 16		
Linear Derating Factor	(Note 6)	P _D	3.9 31	mW/°C	
Thermal Resistance, Junction to Ambient	(Note 7)	В	62.5	°C/W	
Thermal Resistance, Junction to Ambient	(Note 6)	R _{0JA}	32.2		
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C	

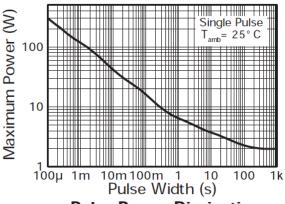
Notes:

- 5. For a device surface mounted on 25mm x 25mm FR-4 PCB with high coverage of single sided 1oz copper, in still air conditions.
- 6. For a device surface mounted on FR-4 PCB measured at t \leq 5 seconds.
- 7. Repetitive rating 25mm x 25mm FR4 PCB, D = 0.05, pulse width 10µs pulse width limited by maximum junction temperature.

Thermal Characteristics







Pulse Power Dissipation



Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage	BV _{DSS}	40	_	_	٧	$I_D = 250\mu A, V_{GS} = 0V$	
Zero Gate Voltage Drain Current		_	_	1	μΑ	V _{DS} = 40V, V _{GS} = 0V	
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS	ON CHARACTERISTICS						
Gate Threshold Voltage	V _{GS(th)}	1		2	V	$I_D = 250 \mu A$, $V_{DS} = V_{GS}$	
Static Drain-Source On-Resistance (Note 9)	D			0.05	Ω	$V_{GS} = 10V, I_D = 4.5A$	
Static Dialii-Source Off-Resistance (Note 9)	R _{DS(ON)}	_		0.075		$V_{GS} = 4.5V, I_D = 3.2A$	
Forward Transconductance (Notes 11)	g fs	_	8.7	_	S	V _{DS} = 15V, I _D = 2.5A	
Diode Forward Voltage (Note 9)	V _{SD}	_	0.8	0.95	V	$I_S = 2.5A$, $V_{GS} = 0V$, $T_J = +25$ °C	
Reverse Recovery Time (Note 11)	t _{rr}		19.86	_	ns	$I_F = 2.5A$, di/dt = 100A/ μ s, $T_J = +25$ °C	
Reverse Recovery Charge (Note 11)	Q _{rr}	_	16.36	_	nC		
DYNAMIC CHARACTERISTICS (Note 10)							
Input Capacitance	C _{iss}	_	770	_	pF	V _{DS} = 40V, V _{GS} = 0V f = 1MHz	
Output Capacitance	Coss	_	92	_	pF		
Reverse Transfer Capacitance	C _{rss}	_	61	_	pF		
Total Gate Charge (Note 11)	Qg	_	18.2	_	nC	$V_{DS} = 30V$, $V_{GS} = 10V$, $I_D = 2.5A$ (refer to test circuit)	
Gate-Source Charge (Note 11)	Q _{gs}	_	2.1	_	nC		
Gate-Drain Charge (Note 11)	Q_{gd}	_	4.5	_	nC		
Turn-On Delay Time (Note 11)	t _{D(on)}	_	2.55	_	ns	$V_{DD} = 30V$, $V_{GS} = 10V$ $I_D = 2.5A$, $R_G \cong 6\Omega$ _ (refer to test circuit)	
Turn-On Rise Time (Note 11)	t _r	_	4.45	—	ns		
Turn-Off Delay Time (Note 11)	t _{D(off)}	_	28.61	_	ns		
Turn-Off Fall Time (Note 11)	t _f	_	7.35	_	ns		

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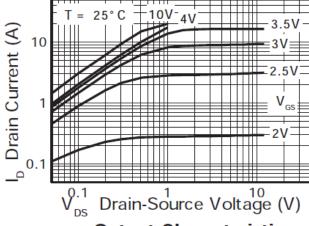
www.diodes.com

Notes:

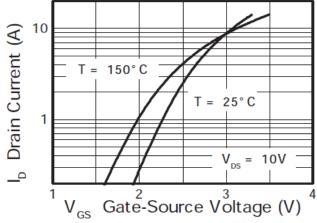
Measured under pulsed conditions. Pulse width ≤ 300µs; duty cycle ≤ 2%.
 Switching characteristics are independent of operating junction temperatures.
 For design aid only, not subject to production testing.



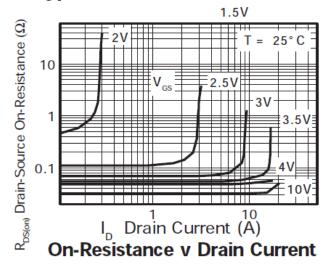
Typical Characteristics

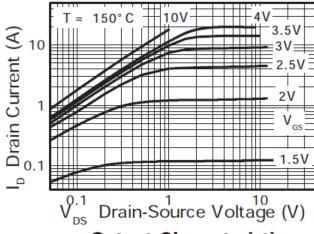


Output Characteristics

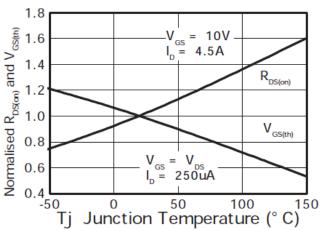


Typical Transfer Characteristics

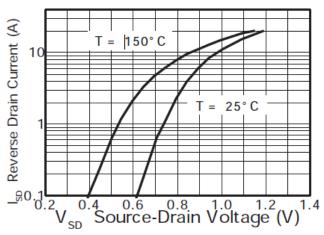




Output Characteristics



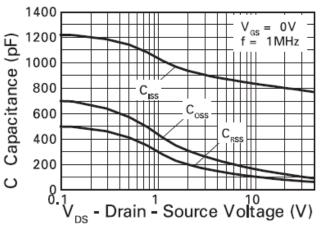
Normalised Curves v Temperature



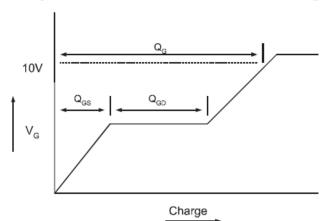
Source-Drain Diode Forward Voltage



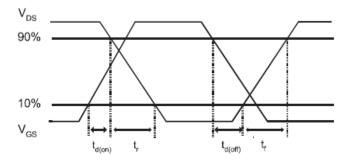
Typical Characteristics (cont.)



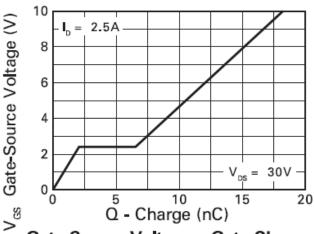
Capacitance v Drain-Source Voltage



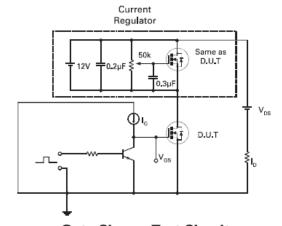
Basic Gate Charge Waveform



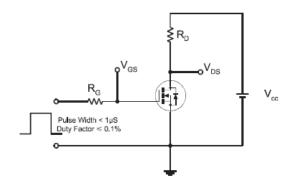
Switching Time Waveforms



Gate-Source Voltage v Gate Charge



Gate Charge Test Circuit

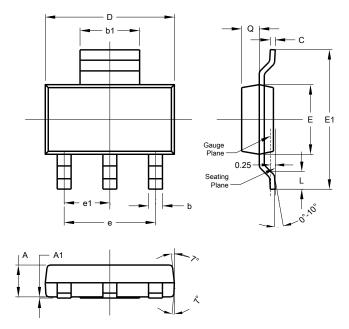


Switching Time Test Circuit



Package Outline Dimensions

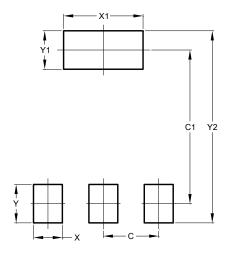
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT223					
Dim	Min	Max	Тур		
Α	1.55	1.65	1.60		
A1	0.010	0.15	0.05		
b	0.60	0.80	0.70		
b1	2.90	3.10	3.00		
С	0.20	0.30	0.25		
D	6.45	6.55	6.50		
Е	3.45	3.55	3.50		
E1	6.90	7.10	7.00		
е	-	-	4.60		
e1	-	-	2.30		
L	0.85	1.05	0.95		
Q	0.84	0.94	0.89		
All Dimensions in mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)		
С	2.30		
C1	6.40		
Х	1.20		
X1	3.30		
Υ	1.60		
Y1	1.60		
Y2	8.00		



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